Abstracts

FET Power Performance Prediction Using a Linearized Device Model

H. Kondoh. "FET Power Performance Prediction Using a Linearized Device Model." 1989 MTT-S International Microwave Symposium Digest 89.2 (1989 Vol. II [MWSYM]): 569-572.

A new model has been developed which, based on a linearized device model, describes the power output at 1 dB gain compression, optimum load impedance and load-pull contours of a FET explicitly in terms of device parameters. Applications of the model to practical devices including commercial MESFET's and a 0.25um-gate MODFET showed agreement with measurements to 40GHz.

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